



SGMNE25230

30V, Power, Single N-Channel, UTDFN Package, MOSFET

FEATURES

- Low On-State Resistance
- Ultra-Low Q_G and Q_{GD}
- ESD Diode Protected Gate
- Ultra-Small Footprint "Tiny FET"
- HBM > 2kV

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNITS
Drain-to-Source Voltage	V_{DS}	30	V
Gate-to-Source Voltage	V_{GS}	± 8	V
Drain Current ⁽¹⁾	I_D	$T_A = +25^\circ\text{C}$	A
		$T_A = +70^\circ\text{C}$	
Drain Current (Pulse) ⁽²⁾	I_{DM}	4.5	A
Total Dissipation	P_D	$T_A = +25^\circ\text{C}$	mW
		$T_A = +70^\circ\text{C}$	
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)		+260	$^\circ\text{C}$

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

NOTES:

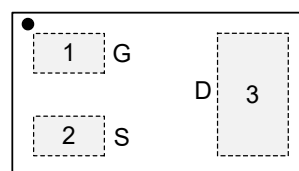
1. The current will be limited by package, PCB, thermal design and operating temperature.
2. $t_{PULSE} < 10\mu\text{s}$.

PRODUCT SUMMARY

$R_{DS(on)}$ (TYP) $V_{GS} = 4.5\text{V}$	$R_{DS(on)}$ (MAX) $V_{GS} = 4.5\text{V}$	I_D (MAX) $T_A = +25^\circ\text{C}$
170m Ω	215m Ω	1.4A

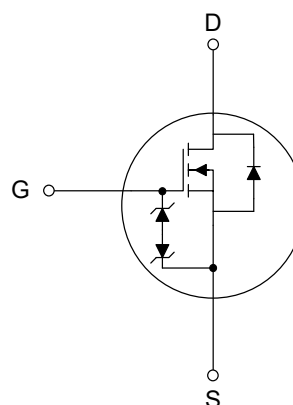
PIN CONFIGURATION

(TOP VIEW)



UTDFN-1x0.6-3L

EQUIVALENT CIRCUIT



APPLICATIONS

- Load Switch Applications
- High-Speed Line Drivers
- Relay Driver Applications
- Handheld and Mobile Applications
- I/O Expansion Switches
- IR Blaster Applications

PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGMNE25230	UTDFN-1×0.6-3L	-55°C to +150°C	SGMNE25230TUEM3G/TR	07X	Tape and Reel, 10000

MARKING INFORMATION

NOTE: X = Date Code.

YY X

Date Code - Quarter

Serial Number

Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

ESD SENSITIVITY CAUTION

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

DISCLAIMER

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

THERMAL RESISTANCE

PARAMETER	SYMBOL	TYP	UNITS
Junction-to-Ambient Thermal Resistance ⁽¹⁾	R _{θJA}	180	°C/W

NOTE: 1. R_{θJA} is determined with the device mounted on one square inch of copper pad, 2oz copper on FR4 board.

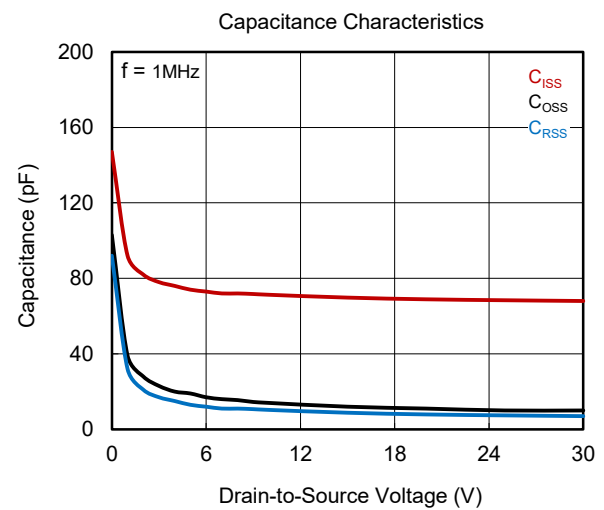
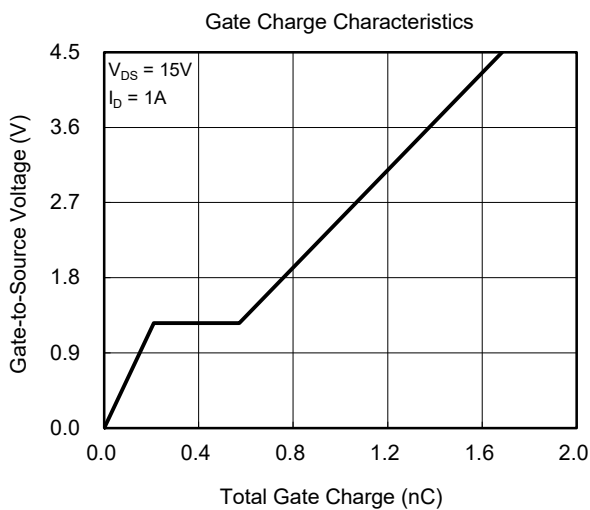
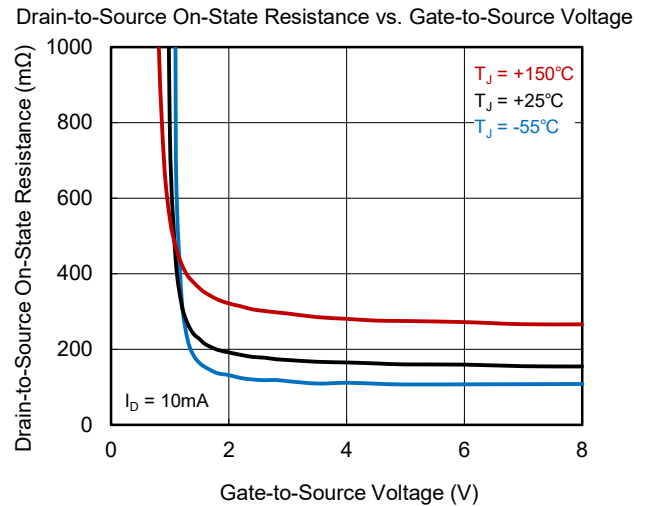
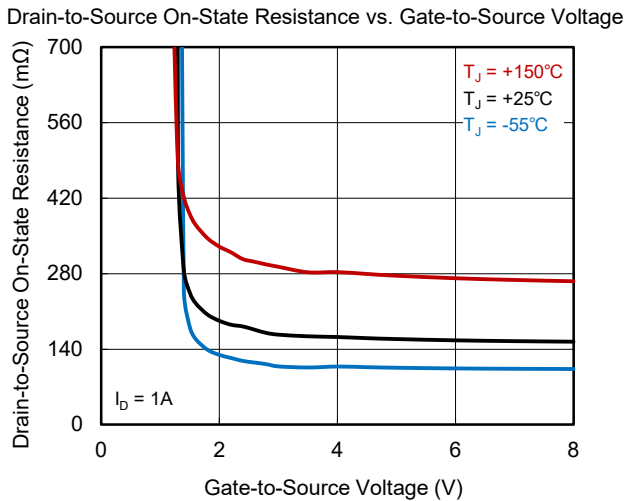
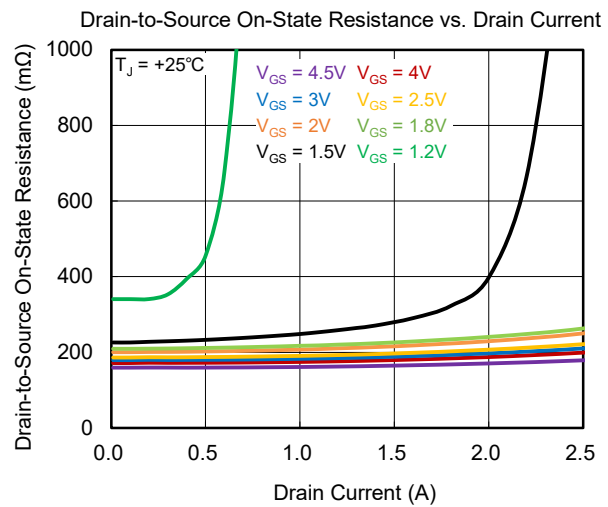
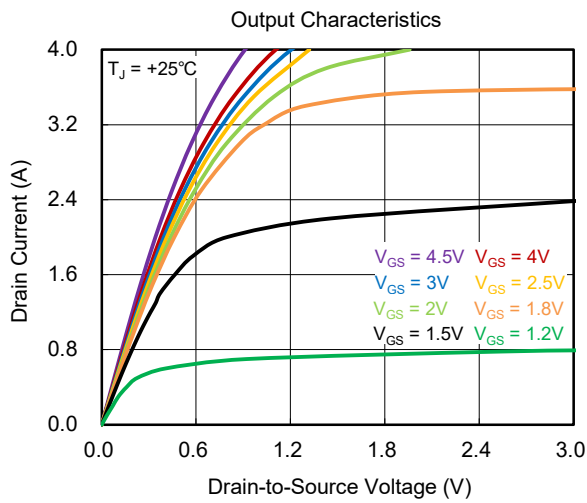
ELECTRICAL CHARACTERISTICS

(T_A = +25°C, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Static OFF Characteristics						
Drain-to-Source Breakdown Voltage	V _{BR_DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0V, V _{DS} = 24V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±10	μA
Static ON Characteristics						
Gate Threshold Voltage	V _{GS_TH}	V _{GS} = V _{DS} , I _D = 250μA	0.4	0.65	1	V
Static Drain-to-Source On-State Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 1A		170	215	mΩ
		V _{GS} = 2.5V, I _D = 0.6A		185	250	
		V _{GS} = 1.8V, I _D = 0.4A		210	280	
		V _{GS} = 1.5V, I _D = 0.1A		235	500	
		V _{GS} = 1.2V, I _D = 10mA		330	700	
Diode Characteristics						
Forward Diode Voltage	V _{FSD}	V _{GS} = 0V, I _S = 1A		0.8	1.2	V
Dynamic Characteristics						
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		70		pF
Output Capacitance	C _{OSS}			12		
Reverse Transfer Capacitance	C _{RSS}			8		
Total Gate Charge	Q _G	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 1A		1.7		nC
Gate-to-Source Charge	Q _{GS}			0.2		
Gate-to-Drain Charge	Q _{GD}			0.4		
Switch Characteristics						
Turn-On Delay Time	t _{D_ON}	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 1A, R _G = 3Ω		10		ns
Rise Time	t _R			33		
Turn-Off Delay Time	t _{D_OFF}			62		
Fall Time	t _F			48		

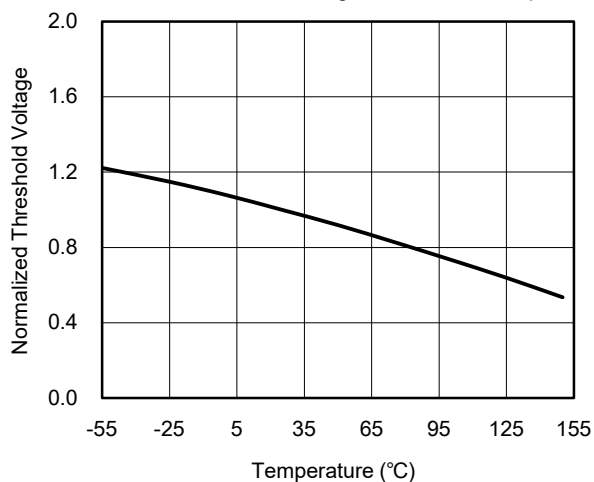
NOTE: 1. Please contact sales for SPICE Model support.

TYPICAL PERFORMANCE CHARACTERISTICS

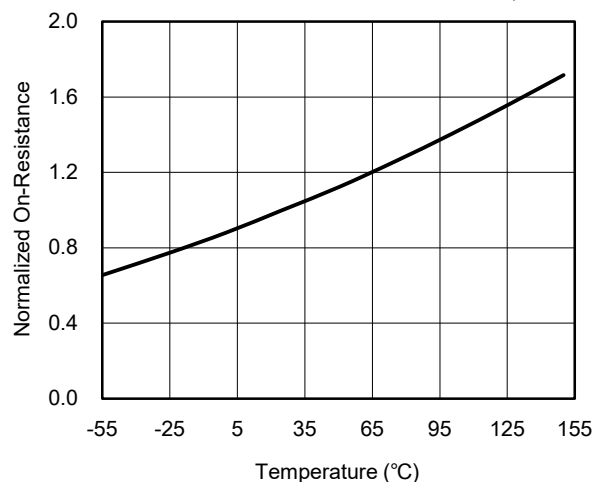


TYPICAL PERFORMANCE CHARACTERISTICS (continued)

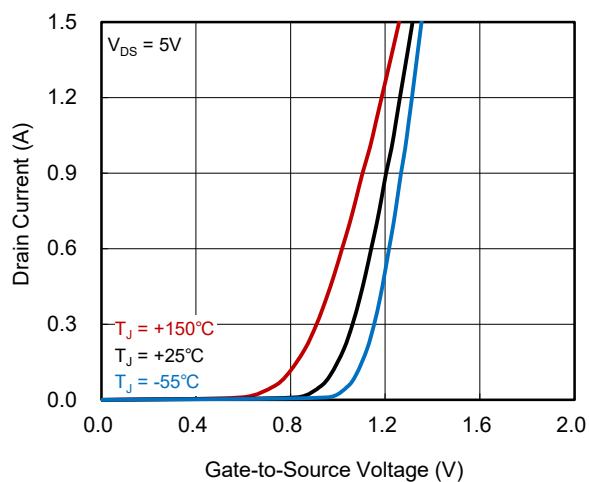
Normalized Threshold Voltage vs. Junction Temperature



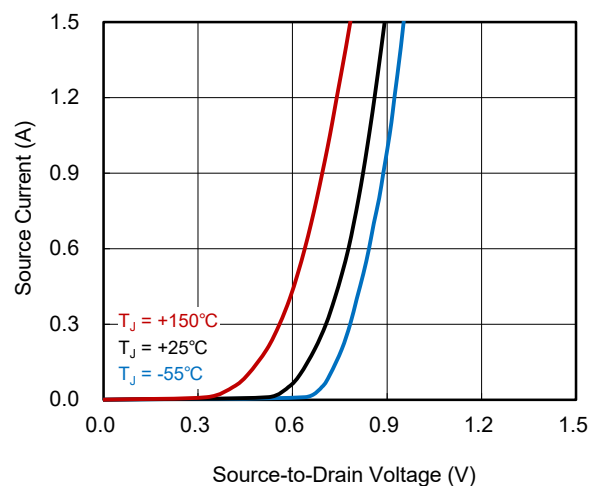
Normalized On-Resistance vs. Junction Temperature



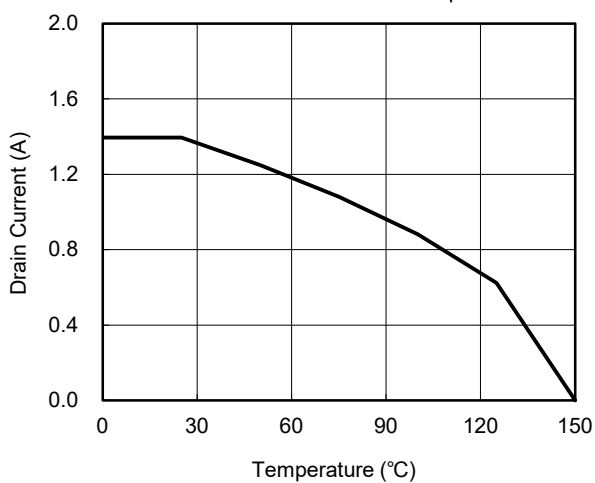
Transfer Characteristics



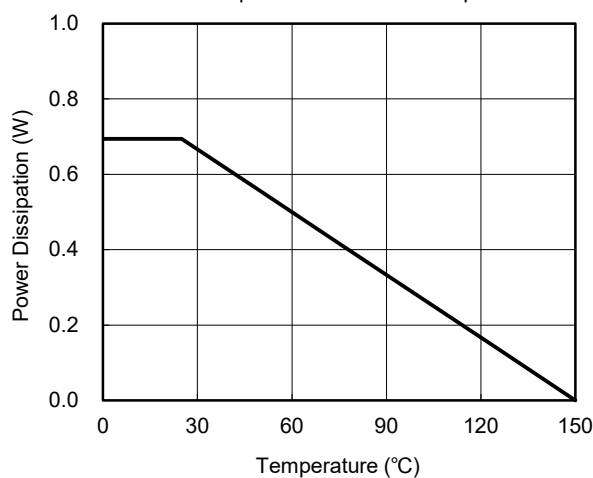
Diode Forward



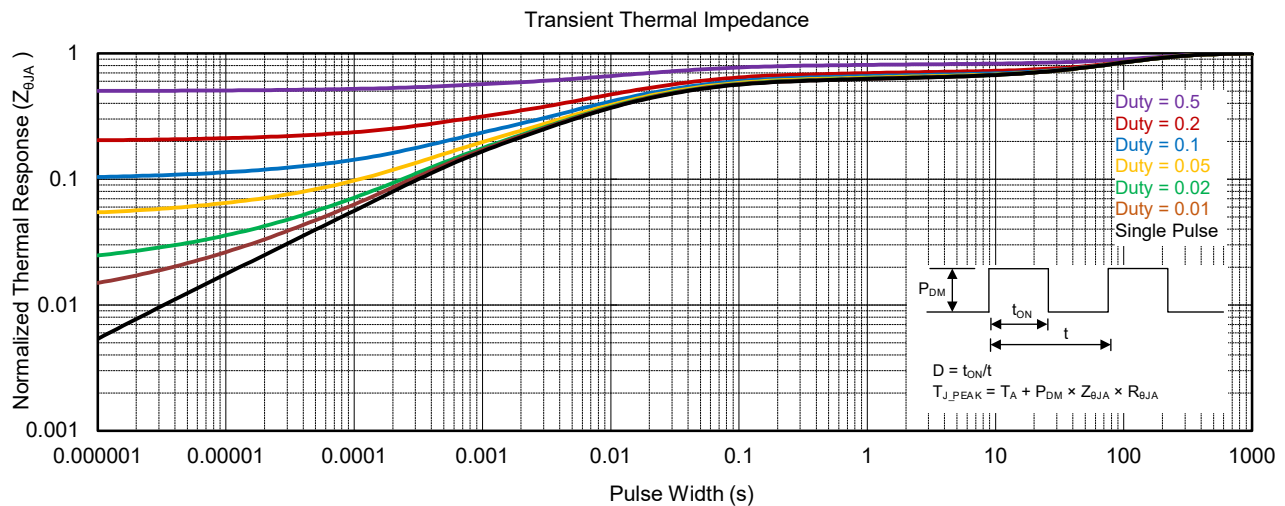
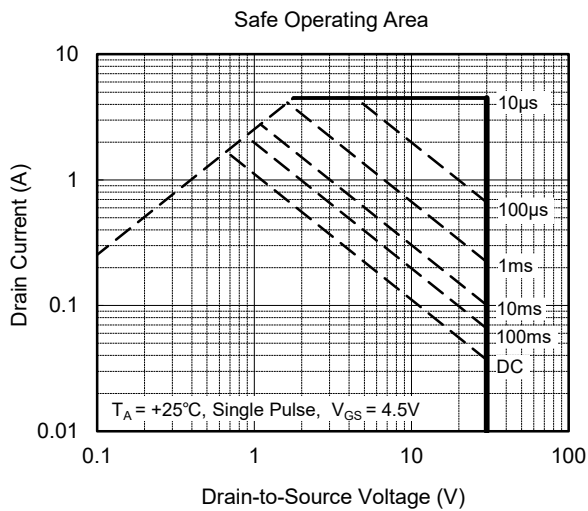
Drain Current vs. Junction Temperature



Power Dissipation vs. Junction Temperature



TYPICAL PERFORMANCE CHARACTERISTICS (continued)



REVISION HISTORY

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

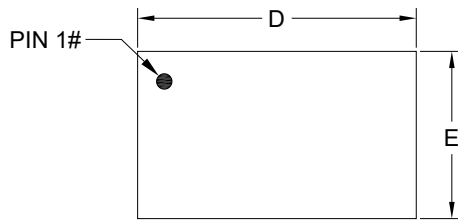
Changes from Original to REV.A (SEPTEMBER 2026)

Changes from Original to REV.A (SEPTEMBER 2026)	Page
Changed from product preview to production data.....	All

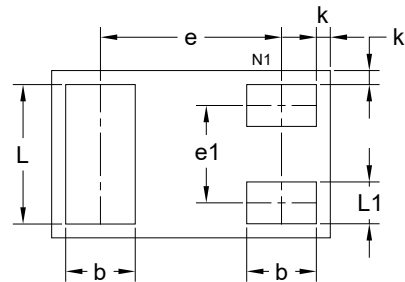
PACKAGE INFORMATION

PACKAGE OUTLINE DIMENSIONS

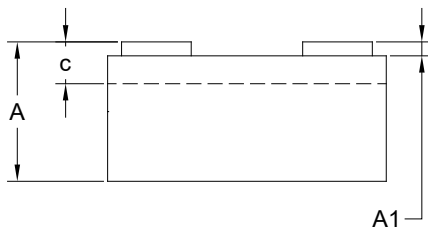
UTDFN-1×0.6-3L



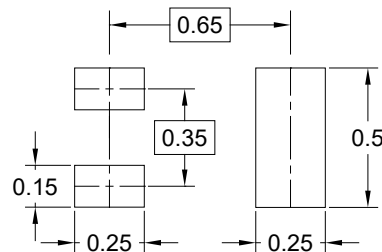
TOP VIEW



BOTTOM VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN (Unit: mm)

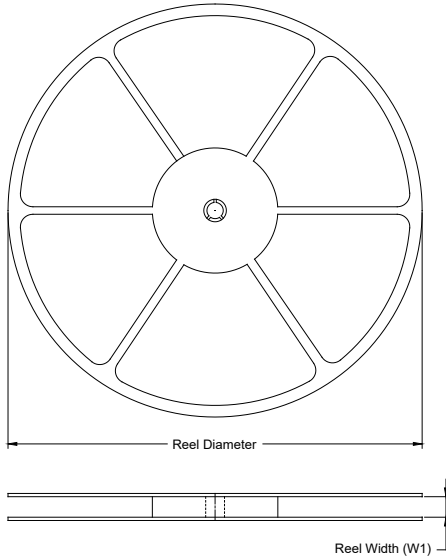
Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	0.400	0.500	0.550
A1	0.000	-	0.050
b	0.200	0.250	0.300
c	0.120	0.150	0.180
D	0.950	1.000	1.050
E	0.550	0.600	0.650
e	0.650 BSC		
e1	0.350 BSC		
k	0.050 REF		
L	0.450	0.500	0.550
L1	0.100	0.150	0.200

NOTE: This drawing is subject to change without notice.

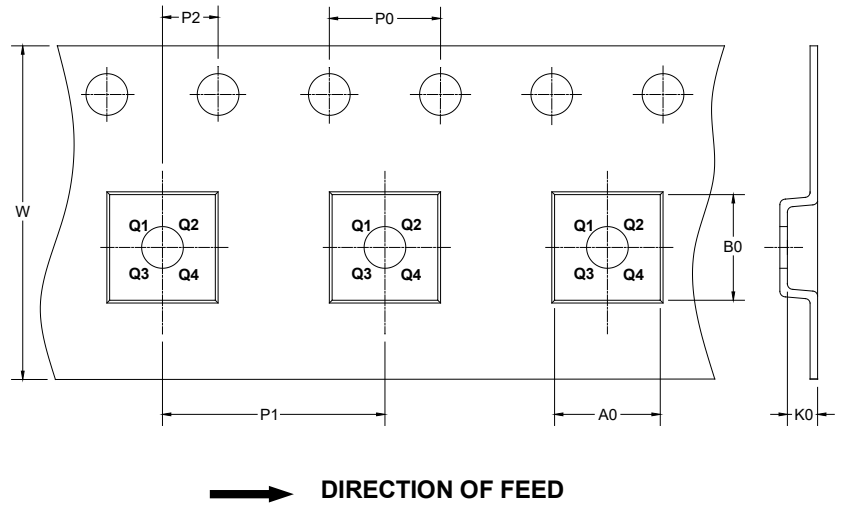
PACKAGE INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

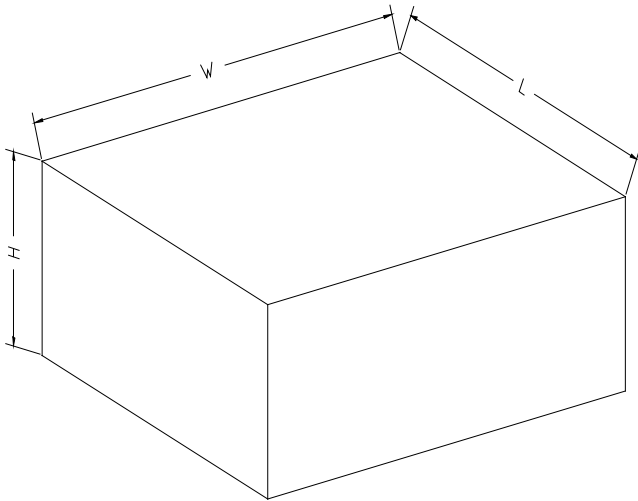
KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
UTDFN-1×0.6-3L	7"	8.6	0.70	1.15	0.57	4.0	2.0	2.0	8.0	Q3

DD0001

PACKAGE INFORMATION

CARTON BOX DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18

DD0002